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FAIRCHILD
### SEMICONDUCTOR ™

Si4532DY*

Dual N- and P-Channel Enhancement Mode Field Effect Transistor

General Description

These dual N- and P-Channel enhancement mode power field effect transistors are produced using Fairchild's propretary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- N-Channel 3.9A, 30V. $R_{DS(ON)}$ = 0.065Ω @V_{GS} = 10V
  $R_{DS(ON)}$ = 0.095Ω @V_{GS} = 4.5V.
- P-Channel -3.5A,-30V. $R_{DS(ON)}$= 0.085Ω @V_{GS} = -10V
  $R_{DS(ON)}$= 0.190 Ω @V_{GS} = -4.5V.

- High density cell design for extremely low $R_{DS(ON)}$.

- High power and current handling capability in a widely used surface mount package.

- Dual (N & P-Channel) MOSFET in surface mount package.
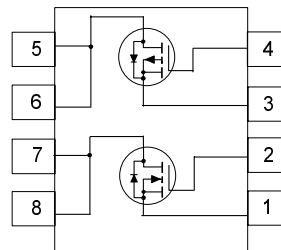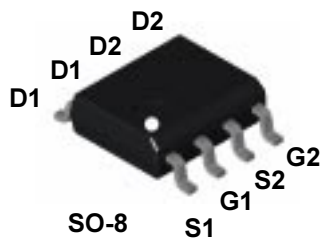
Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		N-Channel	P-Channel	Units
V_{DSS}	Drain-Source Voltage		30	-30	V
V_{GSS}	Gate-Source Voltage		20	-20	V
I_D	Drain Current - Continuous	(Note 1a)	3.9	-3.5	A
	- Pulsed		20	-20	
P_D	Power Dissipation for Dual Operation		2		W
	Power Dissipation for Single Operation	(Note 1a)	1.6		
		(Note 1b)	1		
		(Note 1c)	0.9		
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		62.5	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
4532	Si4532DY	13"	12mm	2500 units

* Die and manufacturing source subject to change without prior notification.

Electrical Characteristics $T_A = 25°C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0$ V, $I_D = 250$ μA	N-Ch	30			V
		$V_{GS} = 0$ V, $I_D = -250$ μA	P-Ch	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24$ V, $V_{GS} = 0$ V	N-Ch			1	μA
		$V_{DS} = -24$ V, $V_{GS} = 0$ V	P-Ch			-1	μA
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20$ V, $V_{DS} = 0$ V	All			100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20$ V, $V_{DS} = 0$ V	All			-100	nA
On Characteristics (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250$ μA	N-Ch	1		3	V
		$V_{DS} = V_{GS}, I_D = -250$ μA	P-Ch	-1		-3	V
$R_{DS(on)}$	Static Drain-Source On Resistance	$V_{GS} = 10$ V, $I_D = 3.9$ A	N-Ch		0.053	0.065	Ω
		$V_{GS} = 4.5$ V, $I_D = 3.1$ A			0.081	0.095	
		$V_{GS} = -10$ V, $I_D = -2.5$ A	P-Ch		0.06	0.085	
		$V_{GS} = -4.5$ V, $I_D = -1.8$ A			0.095	0.19	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10$ V, $V_{DS} = 5$ V	N-Ch	15			A
		$V_{GS} = -10$ V, $V_{DS} = -5$ V	P-Ch	-15			
g_{FS}	Forward Transconductance	$V_{DS} = 15$ V, $I_D = 3.9$ A	N-Ch		7		S
		$V_{DS} = -15$ V, $I_D = -2.5$ A	P-Ch		5		
Dynamic Characteristics							
C_{iss}	Input Capacitance	$V_{DS} = 10$ V, $V_{GS} = 0$ V, f = 1.0 MHz	N-Ch		235		pF
			P-Ch		420		
C_{oss}	Input Capacitance	$V_{DS} = -10$ V, $V_{GS} = 0$ V, f = 1.0 MHz	N-Ch		150		pF
			P-Ch		140		
C_{rss}	Reverse Transfer Capacitance		N-Ch		49		pF
			P-Ch		60		

Electrical Characteristics (continued)

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Switching Characteristics (Note 2)							
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 10 V, I_D = 1 A, V_{GS} = 10 V, R_{GEN} = 6 Ω	N-Ch		7	13	ns
			P-Ch		9	18	
t_r	Turn-On Rise Time		N-Ch		18	29	ns
			P-Ch		8	16	
$t_{d(off)}$	Turn-Off Delay Time	V_{DD} = -10 V, I_D = -2.5 A, V_{GS} = -10 V, R_{GEN} = 6 Ω	N-Ch		15	27	ns
			P-Ch		18	29	
t_f	Turn-Off Fall Time		N-Ch		0.8	8	ns
			P-Ch		6	12	
t_{rr}	Drain-Source Reverse Recovery Time	I_F = 1.7 A, di/dt = 100A/μs	N-Ch			80	nS
		I_F = -1.7 A, di/dt = 100A/μs	P-Ch			80	
Q_g	Total Gate Charge	V_{DS} = 10 V, I_D = 3.9 A, V_{GS} = 10 V	N-Ch		3.7	15	nC
			P-Ch		5	15	
Q_{gs}	Gate-Source Charge	V_{DS} = -10 V, I_D = -2.5 A, V_{GS} = -10 V	N-Ch		0.9		nC
			P-Ch		1.7		
Q_{gd}	Gate-Drain Charge		N-Ch		1.9		nC
			P-Ch		1.8		

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
I_S	Maximum Continuous Drain-Source Diode Forward Current		N-Ch			1.7	A
			P-Ch			-1.7	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 1.7 A (Note 2)	N-Ch		0.75	1.2	V
		V_{GS} = 0 V, I_S = -1.7 A (Note 2)	P-Ch		-0.75	-1.2	V

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) 78° C/W when mounted on a 0.05 in² pad of 2 oz. copper.

b) 125° C/W when mounted on a 0.02 in² pad of 2 oz. copper.

c) 135° C/W when mounted on a minimum mounting pad.
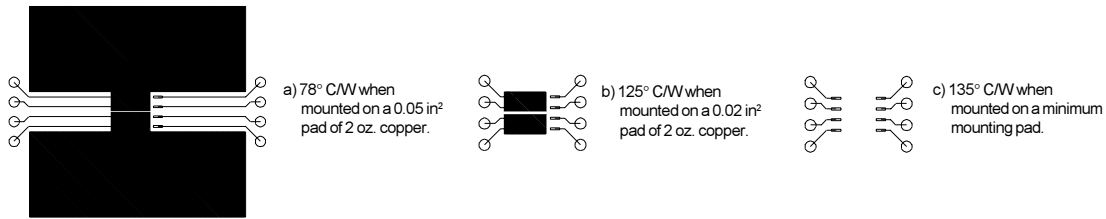
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

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